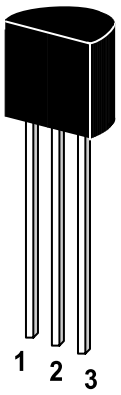
ST 2SA562

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into two group, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	35	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Base Current	$-I_B$	100	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	^{O}C
Storage Temperature Range	T_S	-55 to +150	^{O}C

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Characteristics at T_{amb}=25 ^{o}C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$=1V, $-I_C$=100mA					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
at $-V_{CE}$=6V, $-I_C$=400mA	h_{FE}	25	-	-	-
Collector Cutoff Current at $-V_{CB}$=35V	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}$=5V	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage at $-I_C$=100mA, $-I_B$=10mA	$-V_{CE(sat)}$	-	0.1	0.25	V
Base Emitter Voltage at $-I_C$=100mA, $-V_{CE}$=1V	$-V_{BE}$	-	0.8	1.0	V
Transition Frequency at $-V_{CE}$=6V, $-I_C$=20mA	f_T	-	200	-	MHz
Collector Output Capacitance at $-V_{CB}$=6V, f=1MHz	C_{OB}	-	13	-	pF